# 2SA2202

# ON Semiconductor®

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# **Bipolar Transistor** -100V, -2A, Low VCE(sat) PNP Single PCP

### **Applications**

DC / DC converters, relay drivers, lamp drivers, motor drivers, flash

### **Features**

- · Adoption of FBET, MBIT processes
- Low collector to emitter saturation voltage
- · High allowable power dissipation

- · Large current capacity
- · High-speed switching

### **Specifications**

Absolute Maximum Ratings at Ta=25°C

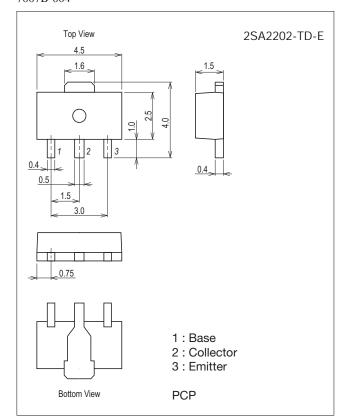
| Parameter                    | Symbol           | Conditions | Ratings | Unit |
|------------------------------|------------------|------------|---------|------|
| Collector to Base Voltage    | V <sub>CBO</sub> |            | -100    | V    |
| Collector to Emitter Voltage | VCES             |            | -100    | V    |
|                              | VCEO             |            | -100    | V    |
| Emitter to Base Voltage      | V <sub>EBO</sub> |            | -7      | V    |
| Collector Current            | IC               |            | -2      | Α    |
| Collector Current (Pulse)    | ICP              |            | -3      | Α    |

Continued on next page.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### **Package Dimensions**

unit: mm (typ) 7007B-004



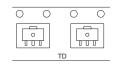
### **Product & Package Information**

• Package : PCP

• JEITA, JEDEC : SC-62, SOT-89, TO-243

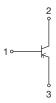
• Minimum Packing Quantity: 1,000 pcs./reel

### Packing Type: TD Marking





### **Electrical Connection**



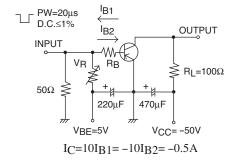
### Continued from preceding page.

| Parameter             | Symbol | Conditions  | Ratings     | Unit |
|-----------------------|--------|---|-------------|------|
| Base Current          | IB     |   | -400        | mA   |
| Callegter Dissipation | PC     | When mounted on ceramic substrate (250mm <sup>2</sup> ×0.8mm) | 1.3         | W    |
| Collector Dissipation |        | Tc=25°C   | 3.5         | W    |
| Junction Temperature  | Tj     |   | 150         | °C   |
| Storage Temperature   | Tstg   |   | -55 to +150 | °C   |

### Electrical Characteristics at Ta=25°C

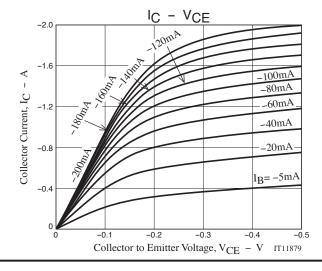
| Parameter                               | Symbol                      | Conditions                                    | Ratings |       |      | Unit |
|---|-----------------------------|---|---------|-------|------|------|
| Parameter                               | Parameter Symbol Conditions |   | min     | typ   | max  | Unit |
| Collector Cutoff Current                | ICBO                        | V <sub>CB</sub> =-80V, I <sub>E</sub> =0A     |         |       | -1   | μΑ   |
| Emitter Cutoff Current                  | IEBO                        | V <sub>EB</sub> =-4V, I <sub>C</sub> =0A      |         |       | -1   | μΑ   |
| DC Current Gain                         | hFE                         | V <sub>CE</sub> =-5V, I <sub>C</sub> =-100mA  | 200     |       | 400  |      |
| Gain-Bandwidth Product                  | fŢ                          | V <sub>CE</sub> =-10V, I <sub>C</sub> =-500mA |         | 300   |      | MHz  |
| Output Capacitance                      | Cob                         | V <sub>CB</sub> =-10V, f=1MHz                 |         | 23    |      | pF   |
| Collector to Emitter Saturation Voltage | V <sub>CE</sub> (sat)       | I <sub>C</sub> =-1A, I <sub>B</sub> =-100mA   |         | -120  | -240 | mV   |
| Base to Emitter Saturation Voltage      | V <sub>BE</sub> (sat)       | I <sub>C</sub> =-1A, I <sub>B</sub> =-100mA   |         | -0.85 | -1.2 | V    |
| Collector to Base Breakdown Voltage     | V(BR)CBO                    | IC=-10μA, IE=0A                               | -100    |       |      | V    |
| Collector to Emitter Breakdown Voltage  | V(BR)CES                    | I <sub>C</sub> =-100μA, R <sub>BE</sub> =0Ω   | -100    |       |      | V    |
|   | V(BR)CEO                    | IC=-1mA, RBE=∞                                | -100    |       |      | V    |
| Emitter to Base Breakdown Voltage       | V(BR)EBO                    | I <sub>E</sub> =-10μA, I <sub>C</sub> =0A     | -7      |       |      | V    |
| Turn-ON Time                            | ton                         |   |         | 40    |      | ns   |
| Storage Time                            | t <sub>stg</sub>            | See specified Test Circuit.                   |         | 600   |      | ns   |
| Fall Time                               | t <sub>f</sub>              |   |         | 30    |      | ns   |

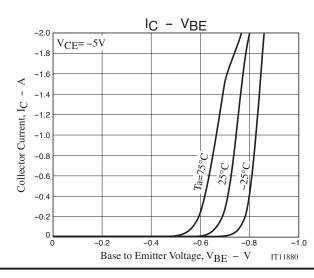
### **Switching Time Test Circuit**

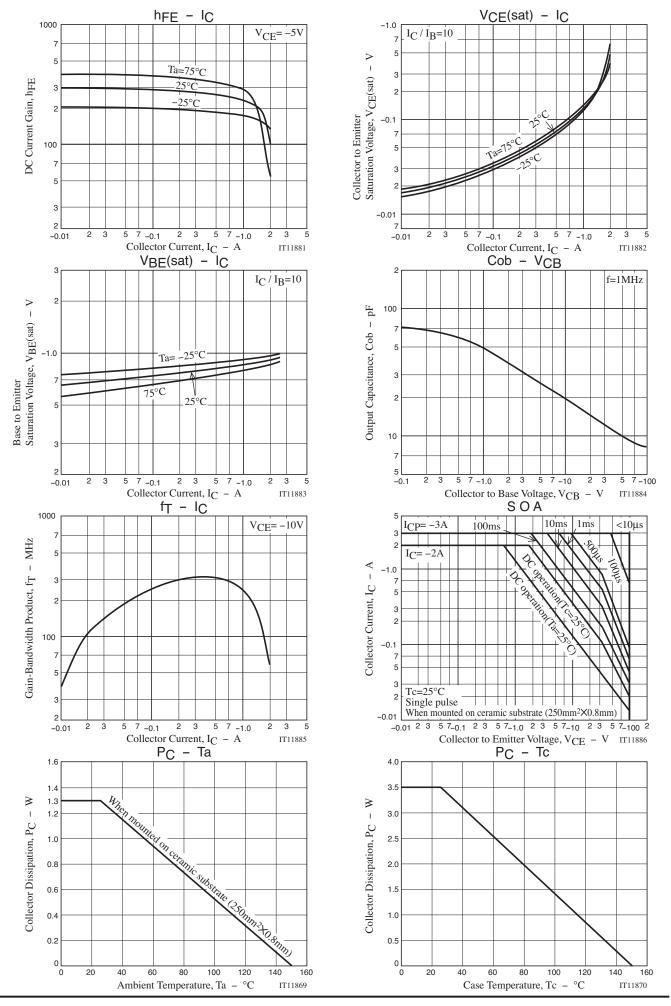


## **Ordering Information**

| Device       | Package | Shipping       | memo    |
|--------------|---------|----------------|---------|
| 2SA2202-TD-E | PCP     | 1,000pcs./reel | Pb Free |





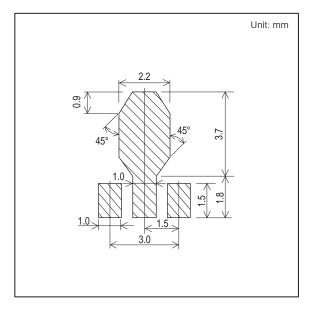


### **Outline Drawing**

2SA2202-TD-E

# Mass (g) Unit 0.058 mm 4. 5±0. 1 1. 5±0. 1 1. 6±0. 2 2. 5±0. 1 0±0. 0±0.2 $0.4^{+0.08}_{-0.05}$ 0. 4±0.03 0. 5+0. 05 1. 5±0. 2 3. 0±0. 2 0.75 0.10 \*1:Lot indication

### Land Pattern Example



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